



Docket No. 740756-1936

#46
Response
Y. Robinson
4/24/03

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:

Shunpei YAMAZAKI et al.

) Group Art Unit: 2812

Serial No. 09/255,777

) Examiner: Richard A. Booth

Filed: February 23, 1999

)

For: SEMICONDUCTOR DEVICE AND METHOD
FOR FORMING THE SAME

) Date: April 16, 2003

TECHNOLOGY CENTER 2800

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Commissioner for Patents
Washington, D.C. 20231

Sir:

In response to the Office Action mailed January 17, 2003, please consider the following remarks provided to traverse the currently pending rejection.

REMARKS

The Office Action of January 17, 2003 was received and carefully reviewed. Reconsideration and withdrawal of the currently pending rejections are requested for the reasons advanced in detail below.

Claims 12, 15, 17, 23, 26, 28, 34-36, 46, 48, 50, 50, 75, 77, 79, 88 and 90-91 are rejected under 35 U.S.C. 103(a) as being unpatentable over Yamazaki U.S. Patent No. 4,727,044 in view of Mukai U.S. Patent No. 5,077,233. This rejection is traversed for the reasons advanced below.

Applicants contend that the combination of Yamazaki and Mukai is not appropriate. Specifically, even if the teachings of Yamazaki and Mukai are combined, this combination fails to teach or suggest the claimed feature of providing at least a channel region of a semiconductor film that is crystallized by laser irradiation through an insulating film. In Mukai, silicon layer 13 is irradiated through the insulating film 14 having an opening 123 (Fig. 4(c)), and a portion of the directly irradiated region becomes a channel region (Fig. 4(f)). That is, the channel region of Mukai is irradiated without the insulating film. In Yamazaki, the channel region 5C is not

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